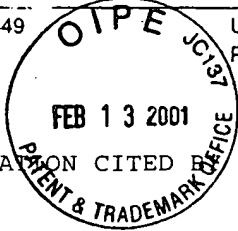


Form PTO-1449	U.S. Department of Commerce Patent and Trademark Office	Atty. Docket No. 99P7722US	Serial No. 09/363,523
 <p>INFORMATION CITED BY APPLICANT</p> <p>(Use several sheets if necessary)</p>		Applicant JAMMY ET AL	
		Filing Date 29-Jul-99	Group 2823

U.S. Patent Documents

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date if appropriate
<i>me</i>	4,277,320	7/7/81	Beguwala	204	164	
<i>me</i>	6,018,174	1/25/00	Schrems	257	296	

Foreign Patent Documents

	Document Number	Date	Country	Class	Subclass	Translation
<i>me</i>	EP 0684637	11/29/95	<i>EP</i>	—	—	
<i>me</i>	EP0637063	2/1/95	<i>EP</i>	—	—	

Other Prior Art (including Author, Title, Date, Pertinent Pages, etc.)

<i>me</i>	XP000687427-YOSHIMARU M ET AL "HIGH QUALITY ULTRA THIN ... " DECEMBER 13, 1992 Pgs 271-274
<i>me</i>	XP000297634 THERMAL NITRIDATION OF SILICON IN A CLUSTER TOOL JANUARY 20, 1992 Pgs 341-343
<i>CME</i>	Yoshimaru, Inoue, Tach, Kurogi, Tamura, Hirasita, Ichikawa and Ino, High Quality Ultra Thin Si ₃ N ₄ Film Selectively Deposited on Poly-Si Electrode by LPCVD with in Situ HF vapor Cleaning, Dec. 13, 1992, IEDM 92-271, Pgs. 271-274
<i>CME</i>	Defino, Fairand Salimian, Thermal Nitridation of silicon in cluster tool. Applied Physics Letters, Jan. 30, 1992, pgs. 341-34
Examiner <i>Michelle Estrada</i>	Date Considered <i>3/26/01</i>